
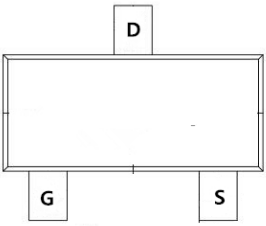
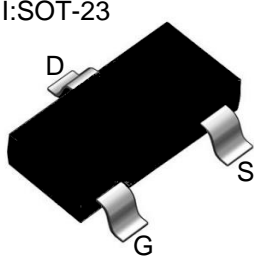
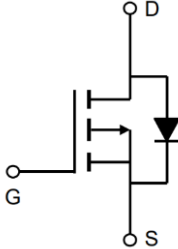


TM3401AI

P-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = -30V$ $I_D = -4.6A$ $R_{DS(ON)} = 40m\Omega$ (Typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Marking: A19T OR 3401

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current	-4.6	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current	-4	A
IDM	Pulsed Drain Current ²	-20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	1.4	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation ³	0.9	W
TSTG	Storage Temperature Range	- 55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	- 55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	85	$^\circ C/W$



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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-32	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.014	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A	---	40	48	mΩ
		V _{GS} =-4.5V, I _D =-3A	---	49	65	
		V _{GS} =-2.5V, I _D =-2A	---	75	85	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.7	-1.1	V
ΔVGS(th)	V _{GS(th)} Temperature Coefficient		---	2.6	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C	---	---	-5	
IGSS	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	5.6	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	11.9	---	nC
Q _{gs}	Gate-Source Charge		---	1.8	---	
Q _{gd}	Gate-Drain Charge		---	3	---	
Td(on)	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-3A	---	6.6	---	ns
T _r	Rise Time		---	27.8	---	
Td(off)	Turn-Off Delay Time		---	46.2	---	
T _f	Fall Time		---	20.6	---	
Ciss	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	290	---	pF
Coss	Output Capacitance		---	73	---	
Crss	Reverse Transfer Capacitance		---	71	---	
IS	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-4.6	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch 2 FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



TM3401AI

P-Channel Enhancement Mosfet

Typical Characteristics

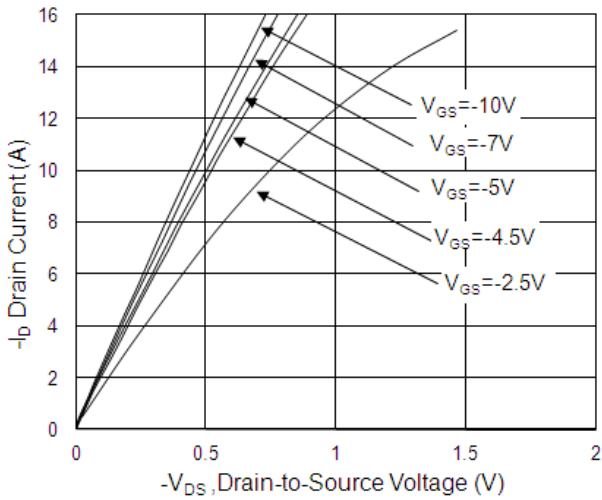


Fig.1 Typical Output Characteristics

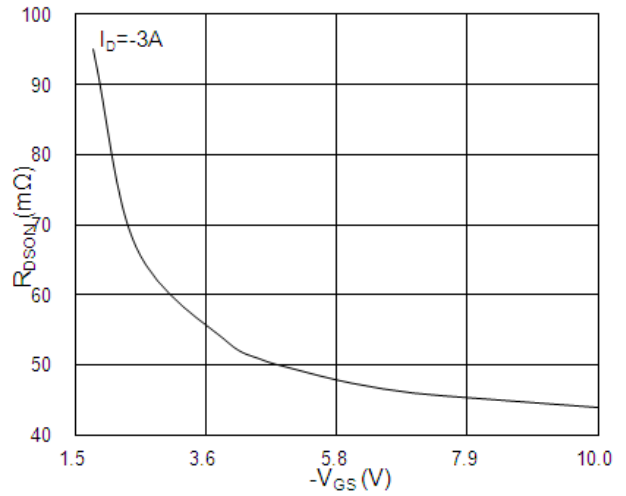


Fig.2 On-Resistance vs. G-S Voltage

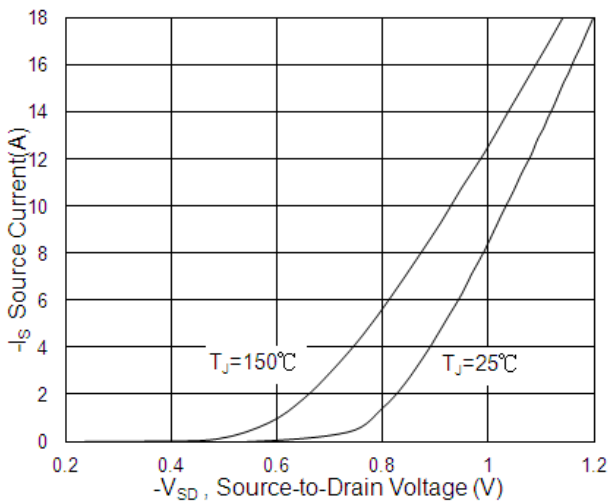


Fig.3 Forward Characteristics Of Reverse

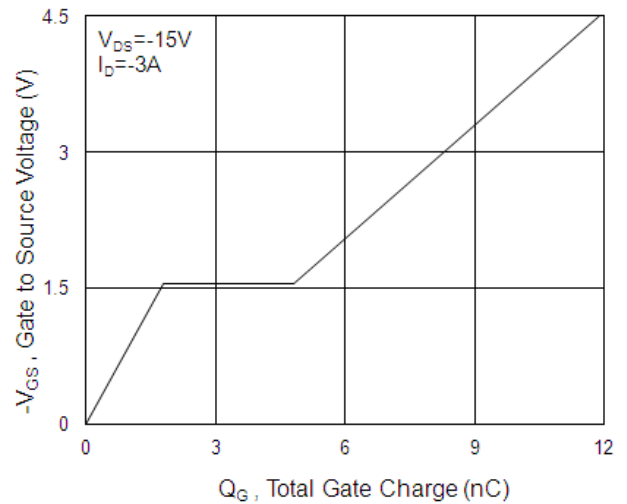


Fig.4 Gate-Charge Characteristics

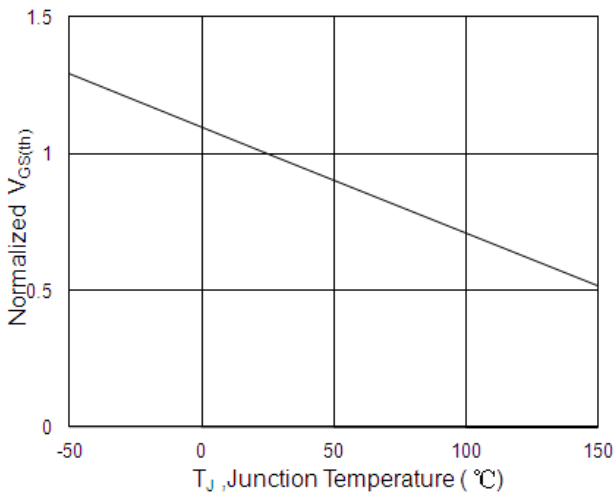


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

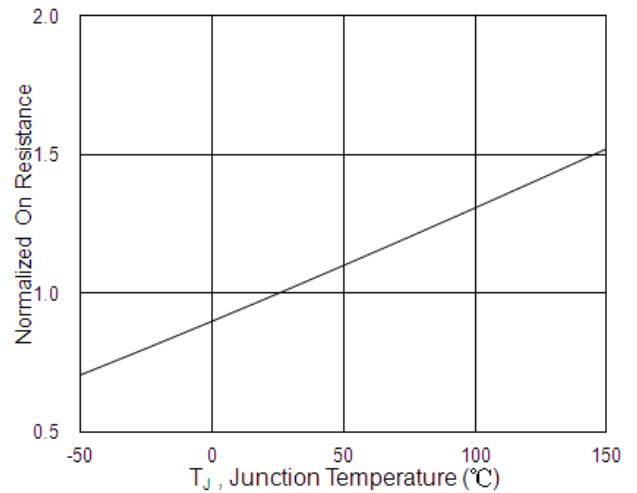


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

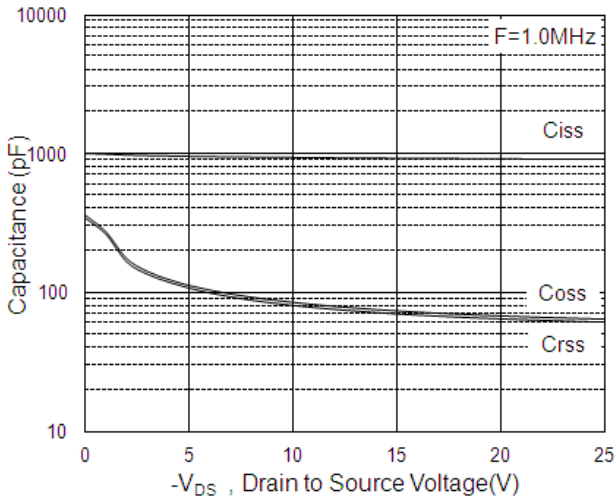


Fig.7 Capacitance

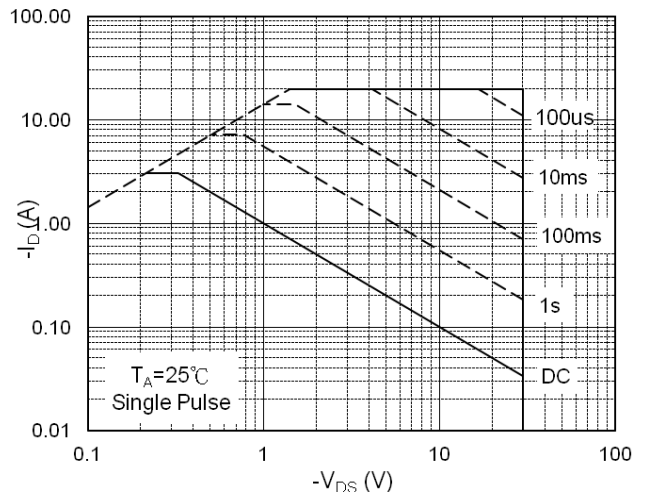


Fig.8 Safe Operating Area

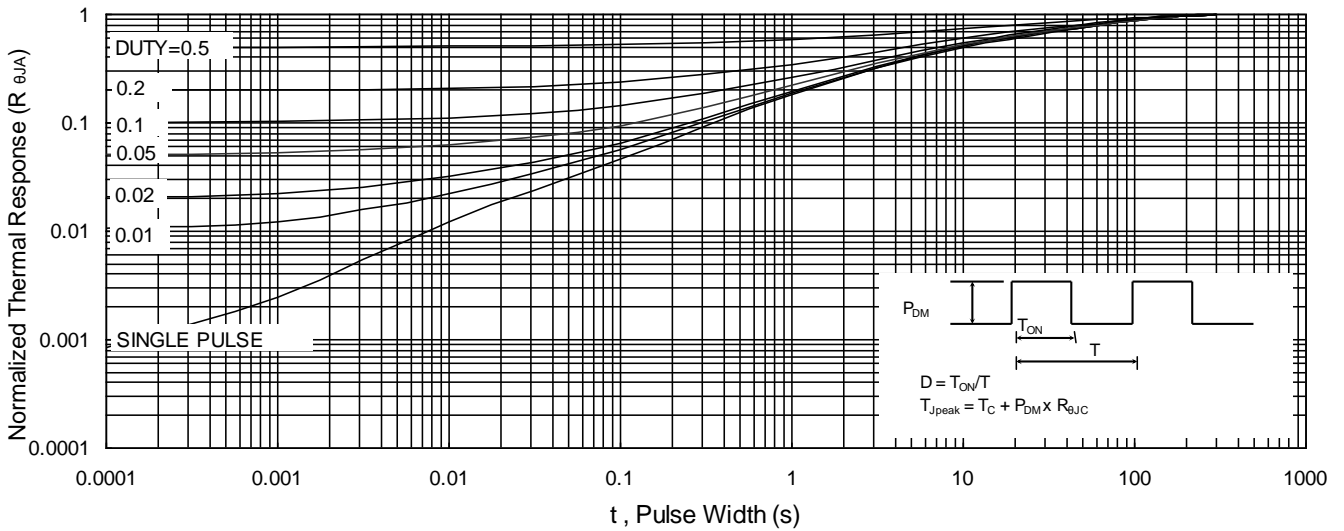


Fig.9 Normalized Maximum Transient Thermal Impedance

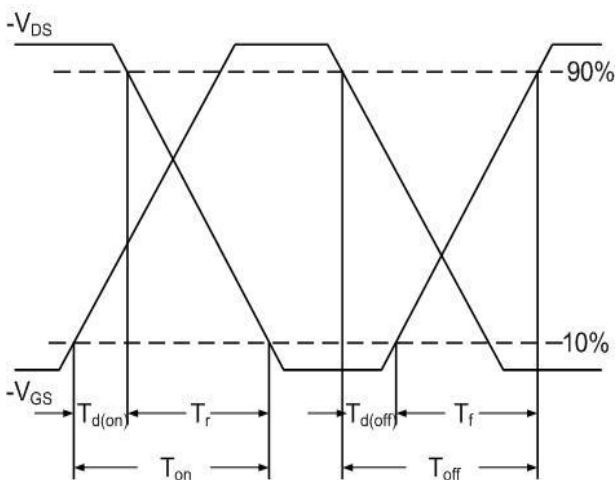


Fig.10 Switching Time Waveform

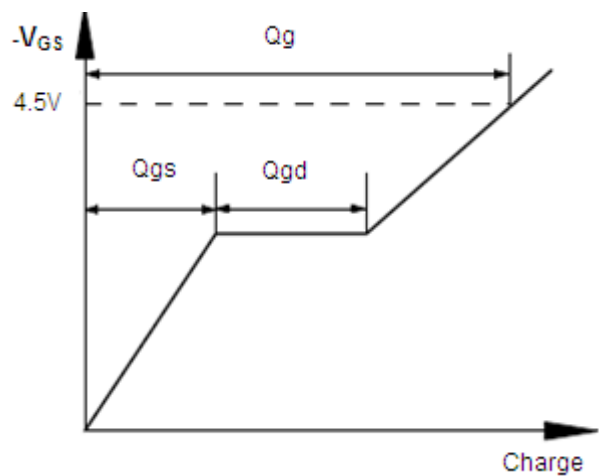
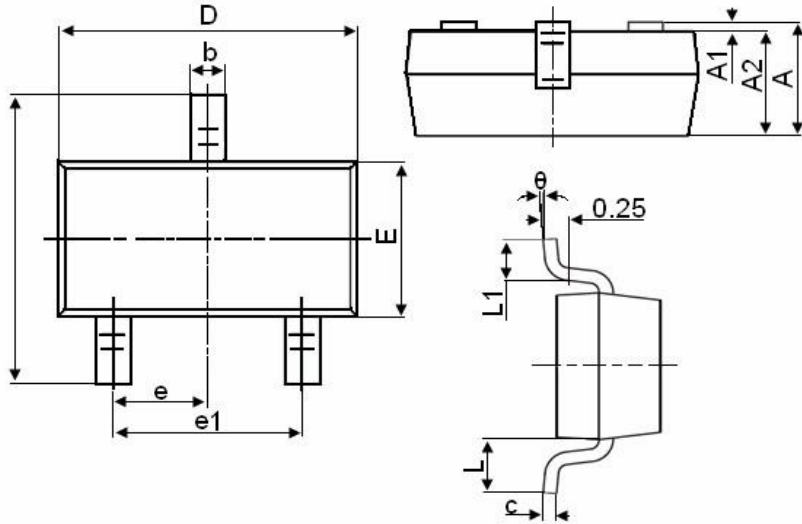


Fig.11 Gate Charge Waveform

Package Mechanical Data:SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°